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Vishay/Siliconix SIRA36DP-T1-GE3

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Distributor of Vishay/Siliconix: Excellent Integrated System Limited

Datasheet of SIRA36DP-T1-GE3 - MOSFET N-CH 30V 40A PPAK SO-8

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SPICE Device Model SiRA36DP

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Vishay Siliconix

N-Channel 30 V (D-S) MOSFET

DESCRIPTION

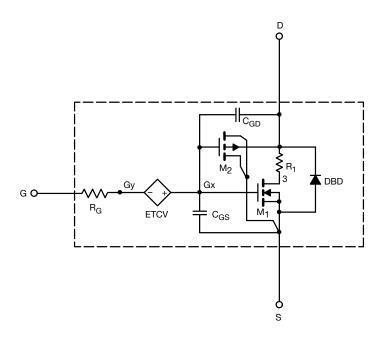
The attached SPICE model describes the typical electrical characteristics of the n-channel vertical DMOS. The sub-circuit model is extracted and optimized over the -55 °C to 125 °C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched $C_{\rm gd}$ model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

CHARACTERISTICS

- N-Channel Vertical DMOS
- Macro Model (Sub-circuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the -55 °C to +125 °C Temperature Range
- Model the Gate Charge

SUBCIRCUIT MODEL SCHEMATIC



Note

• This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

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SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	TEST CONDITIONS	SIMULATED DATA	MEASURED DATA	UNIT
Static					
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.7	-	V
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	0.0023	0.0023	Ω
		V _{GS} = 4.5 V, I _D = 10 A	0.0034	0.0033	
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 10 \text{ V}, I_D = 20 \text{ A}$	99	115	S
Diode Forward Voltage	V_{SD}	I _S = 5 A	0.72	0.73	V
Dynamic ^b					
Input Capacitance	C _{iss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz	2820	2815	pF
Output Capacitance	C _{oss}		847	842	
Reverse Transfer Capacitance	C _{rss}		72	70	
Total Gate Charge	Qg	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 10 \text{ A}$	37	37	nC
			17	17.3	
Gate-Source Charge	Q_{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 10 \text{ A}$	6.8	6.8	
Gate-Drain Charge	Q _{gd}]	3.2	3.2	

Notes

- a. Pulse test; pulse width $\leq 300 \,\mu\text{s}$, duty cycle $\leq 2 \,\%$.
- b. Guaranteed by design, not subject to production testing.

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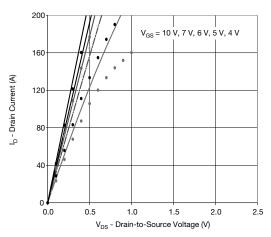
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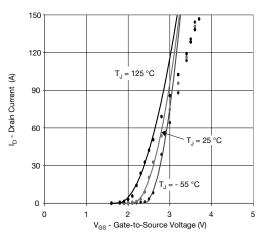


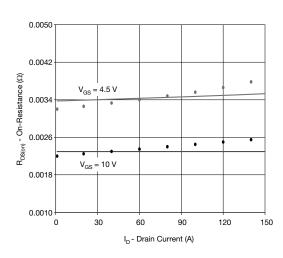
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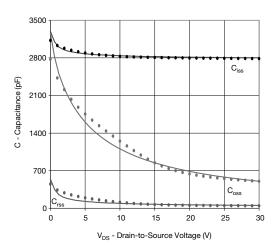
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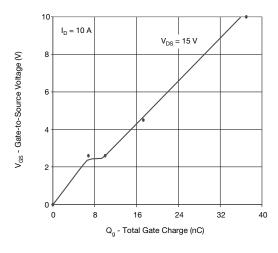
COMPARISON OF MODEL WITH MEASURED DATA (T_J = 25 °C, unless otherwise noted)

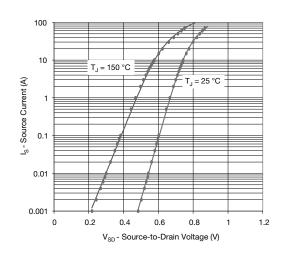












Note

• Dots and squares represent measured data. Copyright: Vishay Intertechnology, Inc.

\$14-0470-Rev. A, 17-Mar-14 3 Document Number: 64322



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